

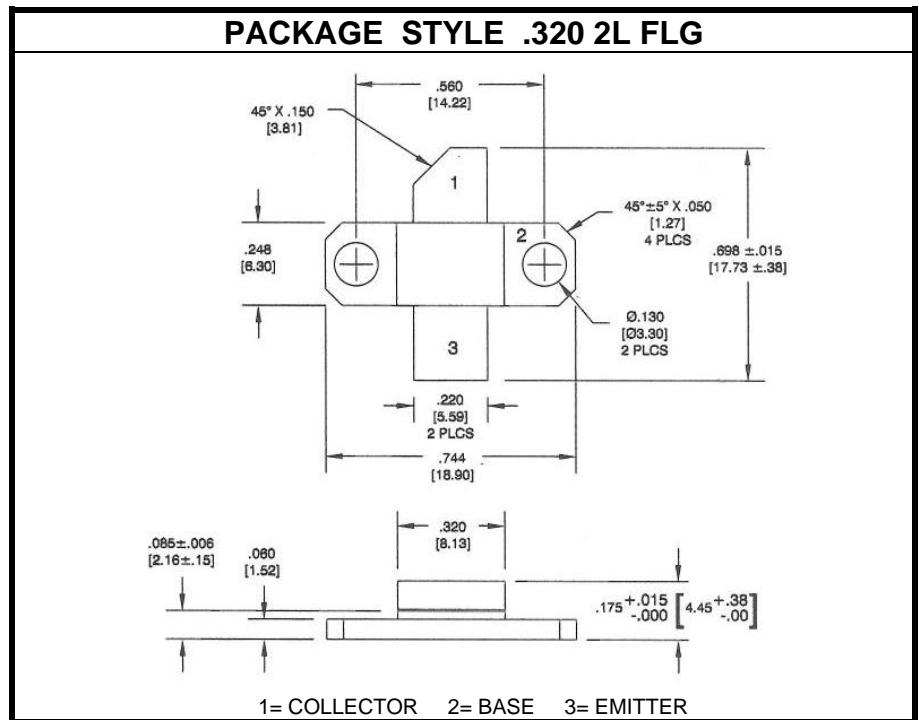
# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **MRA0610-23** is designed for Class C, Common Base Wideband Large Signal Amplifier Applications from 600 MHz to 1.0 GHz, With Internal Compensating Matching Network and Diffused Ballast Resistors.

**MAXIMUM RATINGS**

$I_C$	3.5 A (CONT)
$V_{CES}$	50 V
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	3.0 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 150 \text{ mA}$	50			V
$BV_{EBO}$	$I_E = 2.0 \text{ mA}$	3.5			V
$I_{CBO}$	$V_{CB} = 28 \text{ V}$			3.0	mA
$h_{FE}$	$V_{CE} = 5.0 \text{ V}$ $I_C = 750 \text{ mA}$	10		100	---
$C_{ob}$	$V_{CB} = 28 \text{ V}$ $f = 1.0 \text{ MHz}$			21	pF
$G_{PB}$	$V_{CE} = 28 \text{ V}$ $P_{out} = 23 \text{ W}$ $f = 600 \text{ MHz \& } 1.0 \text{ GHz}$	7.0			dB
$\eta_C$		50			%